

Maria Isabel Alonso

List of Publications by Year in descending order

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149
papers

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109137

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times ranked

8952
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#	ARTICLE	IF	CITATIONS
1	Enhanced Photoluminescence of Cesium Lead Halide Perovskites by Quasi-3D Photonic Crystals. <i>Advanced Optical Materials</i> , 2022, 10, 2101324.	3.6	10
2	Efficient infrared sunlight absorbers based on gold-covered, inverted silicon pyramid arrays. <i>Materials Advances</i> , 2022, 3, 2364-2372.	2.6	2
3	Anisotropic thermoreflectance thermometry: A contactless frequency-domain thermoreflectance approach to study anisotropic thermal transport. <i>Review of Scientific Instruments</i> , 2022, 93, 034902.	0.6	5
4	Quantifying thermal transport in buried semiconductor nanostructures via cross-sectional scanning thermal microscopy. <i>Nanoscale</i> , 2021, 13, 10829-10836.	2.8	12
5	Photoluminescence of Bound Exciton Complexes and Assignment to Shallow Defects in Methylammonium/Formamidinium Lead Iodide Mixed Crystals. <i>Advanced Optical Materials</i> , 2021, 9, 2001969.	3.6	11
6	Observation of second sound in a rapidly varying temperature field in Ge. <i>Science Advances</i> , 2021, 7, .	4.7	40
7	High-Throughput Nanofabrication of Metasurfaces with Polarization-Dependent Response. <i>Advanced Optical Materials</i> , 2020, 8, 2000786.	3.6	13
8	Beating the Thermal Conductivity Alloy Limit Using Long-Period Compositionally Graded Si_xGe_x Superlattices. <i>Journal of Physical Chemistry C</i> , 2020, 124, 19864-19872.	1.5	9
9	Phase Diagram of Methylammonium/Formamidinium Lead Iodide Perovskite Solid Solutions from Temperature-Dependent Photoluminescence and Raman Spectroscopies. <i>Journal of Physical Chemistry C</i> , 2020, 124, 3448-3458.	1.5	42
10	Spectroscopic ellipsometry study of $\text{FA}_{1-x}\text{MA}_x\text{PbI}_3$ hybrid perovskite single crystals. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2019, 37, .	0.6	7
11	Equal Footing of Thermal Expansion and Electron-Phonon Interaction in the Temperature Dependence of Lead Halide Perovskite Band Gaps. <i>Journal of Physical Chemistry Letters</i> , 2019, 10, 2971-2977.	2.1	64
12	Hydroxypropyl cellulose photonic architectures by soft nanoimprinting lithography. <i>Nature Photonics</i> , 2018, 12, 343-348.	15.6	146
13	Ultrathin Semiconductor Superabsorbers from the Visible to the Near-Infrared. <i>Advanced Materials</i> , 2018, 30, 1705876.	11.1	29
14	Self-assembly of polyhedral metal-organic framework particles into three-dimensional ordered superstructures. <i>Nature Chemistry</i> , 2018, 10, 78-84.	6.6	298
15	Comparing the potential of different strategies for colour tuning in thin film photovoltaic technologies. <i>Science and Technology of Advanced Materials</i> , 2018, 19, 823-835.	2.8	11
16	Localized thinning for strain concentration in suspended germanium membranes and optical method for precise thickness measurement. <i>AIP Advances</i> , 2018, 8, 115131.	0.6	3
17	Organic Solar Cells. <i>Springer Series in Optical Sciences</i> , 2018, , 439-461.	0.5	1
18	Organic-Inorganic Hybrid Perovskite Solar Cells. <i>Springer Series in Optical Sciences</i> , 2018, , 463-507.	0.5	2

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19	Optical Properties of Semiconductors. Springer Series in Optical Sciences, 2018, , 89-113.	0.5	3
20	Organic Semiconductors. Springer Series in Optical Sciences, 2018, , 427-469.	0.5	1
21	Pressure-Induced Locking of Methylammonium Cations versus Amorphization in Hybrid Lead Iodide Perovskites. Journal of Physical Chemistry C, 2018, 122, 22073-22082.	1.5	42
22	Conjugated Polymers: Relationship Between Morphology and Optical Properties. Springer Series in Surface Sciences, 2018, , 335-353.	0.3	0
23	A CO ₂ optical sensor based on self-assembled metal-organic framework nanoparticles. Journal of Materials Chemistry A, 2018, 6, 13171-13177.	5.2	62
24	Thermal transport in epitaxial Si _{1-x} Ge _x alloy nanowires with varying composition and morphology. Nanotechnology, 2017, 28, 505704.	1.3	9
25	Controlled Pinning of Conjugated Polymer Spherulites and Its Application in Detectors. Advanced Optical Materials, 2017, 5, 1700276.	3.6	12
26	Spectroscopic imaging ellipsometry of self-assembled SiGe/Si nanostructures. Applied Surface Science, 2017, 421, 547-552.	3.1	1
27	Evaluation of the dielectric function of colloidal Cd _{1-x} Hg _x Te quantum dot films by spectroscopic ellipsometry. Applied Surface Science, 2017, 421, 295-300.	3.1	6
28	Electronic wave functions and optical transitions in (In,Ga)As/GaP quantum dots. Physical Review B, 2016, 94, .	1.1	10
29	Dynamic disorder, phonon lifetimes, and the assignment of modes to the vibrational spectra of methylammonium lead halide perovskites. Physical Chemistry Chemical Physics, 2016, 18, 27051-27066.	1.3	325
30	Experimental and theoretical optical properties of methylammonium lead halide perovskites. Nanoscale, 2016, 8, 6317-6327.	2.8	385
31	Growth and Characterization of Epitaxial In-plane SiGe Alloy Nanowires. Materials Today: Proceedings, 2015, 2, 548-556.	0.9	4
32	Reversible Hydration of CH ₃ NH ₃ PbI ₃ in Films, Single Crystals, and Solar Cells. Chemistry of Materials, 2015, 27, 3397-3407.	3.2	1,133
33	Composition and Strain Imaging of Epitaxial In-Plane SiGe Alloy Nanowires by Micro-Raman Spectroscopy. Journal of Physical Chemistry C, 2015, 119, 22154-22163.	1.5	6
34	Tailoring thermal conductivity by engineering compositional gradients in Si _{1-x} Ge _x superlattices. Nano Research, 2015, 8, 2833-2841.	5.8	31
35	The dielectric tensor of monoclinic 1,3,4,9,10-perylene tetracarboxylic dianhydride in the visible spectral range. Thin Solid Films, 2014, 571, 420-425.	0.8	5
36	On the complex refractive index of polymer:fullerene photovoltaic blends. Thin Solid Films, 2014, 571, 371-376.	0.8	23

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37	Strain-induced fundamental optical transition in (In,Ga)As/GaP quantum dots. Applied Physics Letters, 2014, 104, 011908.	1.5	12
38	Composition dependent nature of the fundamental optical transition in (In, Ga)As/GaP quantum dots., 2014, , .		0
39	Advanced Ellipsometric Characterization of Conjugated Polymer Films. Advanced Functional Materials, 2014, 24, 2116-2134.	7.8	76
40	Using high pressure to unravel the mechanism of visible emission in amorphous Si/SiO _x nanoparticles. Physical Review B, 2014, 89, .	1.1	14
41	Spectroscopic Evaluation of Mixing and Crystallinity of Fullerenes in Bulk Heterojunctions. Advanced Functional Materials, 2014, 24, 6972-6980.	7.8	26
42	Dependence on pressure of the refractive indices of wurtzite ZnO, GaN, and AlN. Physical Review B, 2014, 90, .	1.1	13
43	Poly(3-hexylthiophene) nanowires in porous alumina: internal structure under confinement. Soft Matter, 2014, 10, 3335.	1.2	38
44	Optical properties of ceria/zirconia epitaxial films grown from chemical solutions. Materials Chemistry and Physics, 2013, 138, 462-467.	2.0	18
45	Raman spectroscopy as a probe of molecular order, orientation, and stacking of fluorinated copper phthalocyanine (C ₁₆ CuPc) thin films. Journal of Raman Spectroscopy, 2013, 44, 597-607.	1.2	11
46	Nature of the optical transition in (In,Ga)As(N)/GaP quantum dots (QDs): Effect of QD size, indium composition and nitrogen incorporation. , 2013, , .		0
47	Ultimate nanopatterning of Si substrate using filtered liquid metal alloy ion source-focused ion beam. Thin Solid Films, 2013, 543, 69-73.	0.8	12
48	Probing local strain and composition in Ge nanowires by means of tip-enhanced Raman scattering. Nanotechnology, 2013, 24, 185704.	1.3	21
49	Spatial Distribution of Optical Near-Fields in Plasmonic Gold Sphere Segment Voids. Plasmonics, 2013, 8, 921-930.	1.8	5
50	Effect of Structure and Interlayer Diffusion in Organic Position Sensitive Photodetectors Based on Complementary Wedge Donor/Acceptor Layers. Journal of Nanoscience and Nanotechnology, 2013, 13, 5148-5153.	0.9	4
51	Valence band structure engineering of thin SiGe/Si quantum wells for piezoresistive applications. Physica Status Solidi (B): Basic Research, 2013, 250, 760-764.	0.7	3
52	Modified Stranski-Krastanov growth in Ge/Si heterostructures via nanostenciled pulsed laser deposition. Nanotechnology, 2012, 23, 065603.	1.3	4
53	Influence of alloy inhomogeneities on the determination by Raman scattering of composition and strain in Si _{1-x} Ge _x /Si(001) layers. Journal of Applied Physics, 2012, 112, 023512.	1.1	18
54	Vapour printing: patterning of the optical and electrical properties of organic semiconductors in one simple step. Journal of Materials Chemistry, 2012, 22, 4519.	6.7	16

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55	Surface vs bulk phase transitions in semiconducting polymer films for OPV and OLED applications. Synthetic Metals, 2012, 161, 2570-2574.	2.1	20
56	Phase behaviour of liquid-crystalline polymer/fullerene organic photovoltaic blends: thermal stability and miscibility. Journal of Materials Chemistry, 2011, 21, 10676.	6.7	80
57	In-Plane Epitaxial Growth of Self-Assembled Ge Nanowires on Si Substrates Patterned by a Focused Ion Beam. Crystal Growth and Design, 2011, 11, 3190-3197.	1.4	20
58	Enhanced Fano Resonance in Asymmetrical Au:Ag Heterodimers. Journal of Physical Chemistry C, 2011, 115, 6410-6414.	1.5	83
59	Effects of pulsed laser radiation on epitaxial self-assembled Ge quantum dots grown on Si substrates. Nanotechnology, 2011, 22, 295304.	1.3	17
60	Real-time studies during coating and post-deposition annealing in organic semiconductors. Thin Solid Films, 2011, 519, 2678-2681.	0.8	15
61	Organic position sensitive photodetectors based on lateral donor-acceptor concentration gradients. Applied Physics Letters, 2011, 99, .	1.5	16
62	Pattern transfer optimization for the fabrication of arrays of silicon nanowires. Microelectronic Engineering, 2010, 87, 1479-1482.	1.1	1
63	Pressure dependence of the electronic structure of a [311] piezoelectric $Ga_{1-x}In_x$. Physical Review B, 2010, 82, .	1.1	10.85
64	Reduction of the transverse effective charge of optical phonons in ZnO under pressure. Applied Physics Letters, 2010, 96, .	1.5	43
65	Evidence of quantum confinement effects on interband optical transitions in Si nanocrystals. Physical Review B, 2010, 82, .	1.1	56
66	Optical constants of $Cu_{1-x}In_xGa_{1-x}Se_8$ crystals. Journal of Applied Physics, 2010, 107, 033502.	1.1	12
67	Crystallisation of Amorphous Germanium Thin Films. Journal of Nanoscience and Nanotechnology, 2009, 9, 3013-3019.	0.9	11
68	Polarized Raman study of self-assembled Ge/Si dots under hydrostatic pressure. Physica Status Solidi (B): Basic Research, 2009, 246, 482-485.	0.7	1
69	Measurement of phonon pressure coefficients for a precise determination of deformation potentials in SiGe alloys. Physica Status Solidi (B): Basic Research, 2009, 246, 548-552.	0.7	7
70	Ellipsometric study of crystallization of amorphous Ge thin films embedded in SiO ₂ . Thin Solid Films, 2008, 516, 4277-4281.	0.8	10
71	On the determination of anisotropy in polymer thin films: A comparative study of optical techniques. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1270-1273.	0.8	21
72	Uniaxial anisotropy of organic thin films determined by ellipsometry. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 927-930.	0.8	20

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73	Ellipsometric measurements of quantum confinement effects on higher interband transitions of Ge nanocrystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 888-891.	0.8	4
74	Composition dependence of the phonon strain shift coefficients of SiGe alloys revisited. <i>Applied Physics Letters</i> , 2008, 92, .	1.5	51
75	Imaging optical near fields at metallic nanoscale voids. <i>Physical Review B</i> , 2008, 78, .	1.1	23
76	Exciton-phonon coupling in diindenoperylene thin films. <i>Physical Review B</i> , 2008, 78, .	1.1	91
77	Cross-plane thermal conductivity reduction of vertically uncorrelated Ge ^δ Si quantum dot superlattices. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	24
78	Phonon pressure coefficient as a probe of the strain status of self-assembled quantum dots. <i>Applied Physics Letters</i> , 2007, 91, 081914.	1.5	20
79	Raman scattering interferences as a probe of vertical coherence in multilayers of carbon-induced Ge quantum dots. <i>Physical Review B</i> , 2007, 76, .	1.1	8
80	Site-controlled growth of Ge nanostructures on Si(100) via pulsed laser deposition nanostenciling. <i>Applied Physics Letters</i> , 2007, 91, 113112.	1.5	14
81	Evolution of strain and composition during growth and capping of Ge quantum dots with different morphologies. <i>Nanotechnology</i> , 2007, 18, 475401.	1.3	15
82	SNOM Characterization of Self-Assembled Organic Nanocrystals. <i>AIP Conference Proceedings</i> , 2007, , .	0.3	0
83	Photoluminescence of CdSe quantum dots with Zn _{0.38} Cd _{0.23} Mg _{0.39} Se barriers under hydrostatic pressure. <i>Physica Status Solidi (B): Basic Research</i> , 2007, 244, 397-401.	0.7	2
84	Raman scattering of capped and uncapped carbon-induced Ge dots under hydrostatic pressure. <i>Physica Status Solidi (B): Basic Research</i> , 2007, 244, 76-81.	0.7	5
85	Strain profile of the wall of semiconductor microtubes: A micro-Raman study. <i>Physica Status Solidi (B): Basic Research</i> , 2007, 244, 380-385.	0.7	0
86	Growth dynamics of C-induced Ge dots on Si _{1-x} Gex strained layers. <i>Surface Science</i> , 2007, 601, 2783-2786.	0.8	5
87	Nanocalorimetric high-temperature characterization of ultrathin films of a-Ge. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 806-811.	1.9	14
88	Spectral ellipsometry of a nanodiamond composite. <i>Semiconductors</i> , 2006, 40, 829-833.	0.2	3
89	Influence of Si interdiffusion on carbon-induced growth of Ge quantum dots: a strategy for tuning island density. <i>Nanotechnology</i> , 2006, 17, 2602-2608.	1.3	17
90	Probing residual strain in InGaAs ^δ GaAs micro-origami tubes by micro-Raman spectroscopy. <i>Journal of Applied Physics</i> , 2006, 99, 063512.	1.1	23

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91	Size-dependent strain effects in self-assembled CdSe quantum dots with Zn _{0.38} Cd _{0.23} Mg _{0.39} Se barriers. Applied Physics Letters, 2006, 89, 231109.	1.5	5
92	Density control on self-assembling of Ge islands using carbon-alloyed strained SiGe layers. Applied Physics Letters, 2006, 89, 101921.	1.5	18
93	Strain and composition profiles of self-assembled Ge ⁺ Si(001) islands. Journal of Applied Physics, 2005, 98, 033530.	1.1	42
94	Self-organization of phthalocyanines on Al ₂ O ₃ (1120) in aligned and ordered films. Journal of Materials Research, 2004, 19, 2061-2067.	1.2	18
95	Optical properties of anisotropic materials: an experimental approach. Thin Solid Films, 2004, 455-456, 124-131.	0.8	19
96	Structure, morphology, and optical properties of thin films of F16CuPc grown on silicon dioxide. Organic Electronics, 2004, 5, 135-140.	1.4	36
97	Spectral ellipsometry of amorphous hydrogenated carbon grown by magnetron sputtering of graphite. Semiconductors, 2003, 37, 1211-1213.	0.2	0
98	Chalcogenide glass-based rib ARROW waveguide. Journal of Non-Crystalline Solids, 2003, 326-327, 455-459.	1.5	23
99	Strong optical anisotropies of F16CuPc thin films studied by spectroscopic ellipsometry. Journal of Chemical Physics, 2003, 119, 6335-6340.	1.2	37
100	Optical and magneto-optical properties of Fe nanoparticles. Physical Review B, 2002, 65, .	1.1	48
101	Controlled Molecular Alignment in Phthalocyanine Thin Films on Stepped Sapphire Surfaces. Advanced Functional Materials, 2002, 12, 455-460.	7.8	62
102	Optical functions of chalcopyrite CuGa _x In _{1-x} Se ₂ alloys. Applied Physics A: Materials Science and Processing, 2002, 74, 659-664.	1.1	160
103	Effect of strain and ordering on the band-gap energy of InGaP. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 88, 139-142.	1.7	7
104	Anisotropic optical properties of single crystalline PTCDA studied by spectroscopic ellipsometry. Organic Electronics, 2002, 3, 23-31.	1.4	63
105	Epitaxial growth of AlN on sapphire (0001) by sputtering: a structural, morphological and optical study. Journal of Crystal Growth, 2002, 242, 116-123.	0.7	34
106	Optical functions and electronic structure of CuInSe ₂ , CuGaSe ₂ , CuInS ₂ , and CuGaS ₂ . Physical Review B, 2001, 63, .	1.1	278
107	Optical transitions near the band edge in bulk CuIn _x Ga _{1-x} Se ₂ from ellipsometric measurements. Materials Chemistry and Physics, 2001, 70, 300-304.	2.0	35
108	Influence of tensile and compressive strain on the band gap energy of ordered InGaP. Applied Physics Letters, 2001, 79, 2758-2760.	1.5	10

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109	Optical studies of gap, hopping energies, and the Anderson-Hubbard parameter in the zigzag-chain compound SrCuO ₂ . Physical Review B, 2001, 63, .	1.1	20
110	Optical properties of CuAlSe ₂ . Journal of Applied Physics, 2000, 88, 1923-1928.	1.1	29
111	Optical properties of chalcopyrite CuAl _x In _{1-x} Se ₂ alloys. Journal of Applied Physics, 2000, 88, 5796-5801.	1.1	45
112	Caracterización estructural mediante elipsometría espectral de multicapas basadas en SiO ₂ . Boletín De La Sociedad Española De Cerámica Y Vidrio, 2000, 39, 729-734.	0.9	0
113	Ellipsometry on Very Thick Multilayer Structures. Physica Status Solidi (B): Basic Research, 1999, 215, 247-251.	0.7	9
114	Characterisation of complex multilayer structures using spectroscopic ellipsometry. European Physical Journal Special Topics, 1999, 09, Pr8-1195-Pr8-1202.	0.2	0
115	Doping dependence of the ellipsometric spectra of Nd _{2-x} Ce _x CuO ₄ single crystals. Physica C: Superconductivity and Its Applications, 1998, 299, 41-51.	0.6	5
116	Structural and optical investigation of GaInAs/GaAs {h 11} structures grown by molecular beam epitaxy. Materials Science and Technology, 1998, 14, 1279-1282.	0.8	1
117	Ellipsometric characterisation of ordered Ga _{0.5} In _{0.5} P. Materials Science and Technology, 1998, 14, 1283-1285.	0.8	1
118	Ellipsometric measurement of the dielectric tensor of Nd _{2-x} Ce _x CuO ₄ . Physical Review B, 1997, 55, 3216-3221.	1.1	9
119	Origin of strong intrinsic Kerr effect in FePt and FePd ordered compounds. IEEE Transactions on Magnetism, 1997, 33, 3220-3222.	1.2	21
120	Optical determination of growth variants in ordered GaInP. Solid State Communications, 1997, 101, 757-760.	0.9	8
121	Aspects of low heterostructure symmetry in (311)A (In,Ga)As/GaAs. Journal of Crystal Growth, 1995, 150, 482-486.	0.7	2
122	Excitonic properties of isolated nanometer-sized InAs islands in a GaAs matrix. Journal of Applied Physics, 1995, 78, 1980-1983.	1.1	16
123	Anisotropies in the structural properties of strained (311) (In,Ga)As/GaAs-heterostructures. Journal Physics D: Applied Physics, 1995, 28, A159-A163.	1.3	2
124	Determination of the dielectric tensor in anisotropic materials. Applied Physics Letters, 1995, 67, 596-598.	1.5	16
125	Spin orientation by optical pumping in In _x Ga _{1-x} As/AlAs multiple quantum wells. Solid State Communications, 1994, 91, 703-707.	0.9	0
126	Optical investigation of the electronic structure of single ultrathin InAs layers grown pseudomorphically on (100) and (311)AGaAs substrates. Physical Review B, 1994, 50, 1628-1635.	1.1	36

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127	Growth and characterization of AlAs/GaInAs multiple quantum wells. Journal of Crystal Growth, 1993, 127, 611-615.	0.7	3
128	Optical characterization of InAs monolayer structures grown on (113)A and (001) GaAs substrates. Applied Physics Letters, 1993, 62, 1000-1002.	1.5	15
129	Investigation of InAs submonolayer and monolayer structures on GaAs(100) and (311) substrates. Journal of Applied Physics, 1993, 74, 7188-7197.	1.1	30
130	Piezoelectric-field-induced localization of barrier states in {211}-oriented InAs/GaAs superlattices. Physical Review B, 1993, 47, 12945-12948.	1.1	7
131	Band-edge states and valence-band offset of GaP/InP strained-layer superlattices. Physical Review B, 1993, 47, 16299-16304.	1.1	12
132	Local Phonons in Strained Superlattices. , 1993, , 73-82.		0
133	Raman-scattering study of GaP/InP strained-layer superlattices. Physical Review B, 1992, 45, 9054-9058.	1.1	16
134	Modulation excitation spectroscopy: A method to determine the symmetry of electronic states. Applied Physics Letters, 1992, 60, 3277-3279.	1.5	2
135	Difference frequency Raman scattering and confined optical phonons in ultrashort-period (GaAs) _n /(AlAs) _n superlattices. Solid State Communications, 1992, 84, 275-279.	0.9	8
136	Optical characterization of AlAs/GaInAs multiple quantum wells. Superlattices and Microstructures, 1992, 12, 207-210.	1.4	2
137	High-resolution Raman spectroscopy of Ge-rich-Ge _{1-x} Si _x alloys: Features of the Ge-Ge vibrational modes. Physical Review B, 1991, 44, 13120-13123.	1.1	16
138	Space groups of Ge/Si superlattices grown along the [110], [111], [112], [120], and [114] directions. Solid State Communications, 1990, 74, 347-351.	0.9	18
139	DETECTION OF DISLOCATION-RELATED PHOTOLUMINESCENCE BANDS IN SI-GE ALLOYS GROWN BY LIQUID PHASE EPITAXY. , 1990, , 1453-1457.		14
140	Raman spectra of Si _n Ge _m superlattices: Theory and experiment. Journal of Applied Physics, 1989, 66, 5645-5648.	1.1	42
141	Resonant Raman scattering in short-period (Si) _n /(Ge) _m superlattices. Physical Review B, 1989, 40, 1361-1364.	1.1	38
142	Space groups and lattice dynamics of Ge/Si superlattices grown in the [001] direction. Solid State Communications, 1989, 69, 479-483.	0.9	86
143	Near-band-gap photoluminescence of Si-Ge alloys. Physical Review B, 1989, 40, 5683-5693.	1.1	524
144	Optical spectra of Si _n Ge _m alloys. Journal of Applied Physics, 1989, 65, 2827-2832.	1.1	245

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145	Raman spectra of $\text{Si}_{1-x}\text{Ge}_x$ alloys. <i>Physical Review B</i> , 1989, 39, 10056-10062.	1.1	404
146	Resonance Raman scattering in pure and ultraheavily doped p-type germanium. <i>Physical Review B</i> , 1988, 37, 10107-10110.	1.1	8
147	Growth of $\text{Si}_{1-x}\text{Ge}_x$ on silicon by liquid phase epitaxy. <i>Journal of Applied Physics</i> , 1987, 62, 4445-4449.	1.1	36
148	Properties of SiGe Alloys Grown on Si Substrates by Liquid Phase Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1987, 102, 419.	0.1	2
149	Liquid Phase Epitaxy of $\text{Si}_{1-x}\text{Ge}_x$ ($0 < x < 1$) On Partially Masked Si-Substrates. <i>Materials Research Society Symposia Proceedings</i> , 1987, 91, 393.	0.1	6